



Patent No. 1449 (Modified)  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No. NOVLP033X1/NVLS-000498X1 Applicant: Lee et al. Filing Date August 26, 2003	Application No.: 10/649,351  Group 1762
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#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
lm	A1	6,551,929	04.2003	Kori et al.			
	A2	6,099,904	08.2000	Mak et al.			
	A3	5,227,329	07.1993	Kobayashi et al.			
	A4	6,017,818	01.2000	Lu, Jiong-Ping			
	A5	6,355,558	03.2002	Dixit et al.			
	A6	6,001,729	12.1999	Shinriki et al.			
	A7	6,844,258	01.18.05	Fair et al.			
	A8	6,174,812 /	01/16/01	Hsiung, et al.			
	A9	6,566,250 /	05/20/03	Tu, et al.			
	A10	6,566,262	05/20/03	Rissman, et al.			
	A11	6,706,625 /	03/16/04	Sudijono, et al.			
	A12	2004/0044127	03.04.04	Okubo et al.			
	A13	2004/0206267	10.21.04	Sambasivan et al.			

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
lm	C1	U.S. Office Action mailed July 12, 2005, from U.S. Application No. 10/815,560/ [Atty Dkt. NOVLP096/NVLS-2902]. /
lm	C2	Wongsenakhum et al., "Method of Forming Low-Resistivity Tungsten Interconnects", Novellus Systems, Inc., filed March 31, 2004, Application No. 10/815,560, pages 1-30. [Atty Dkt. NOVLP096/NVLS-2902] /
lm	C3	U.S. Office Action mailed July 17, 2002, from U.S. Application No. 09/975,074/ [Atty Dkt. NOVLP033/NVLS-000498]. /
lm	C4	Presentation by Inventor James Fair: "Chemical Vapor Deposition of Refractory Metal Silicides," 27 Pages, 1983 /
lm	C5	Saito et al., "A Novel Copper Interconnection Technology Using Self Aligned Metal Capping Method," IEEE, 3 Pages, 2001 /
lm	C6	U.S. Office Action mailed June 22, 2004, from U.S. Application No. 10/435,010/ [Atty Dkt. NOVLP058/NVLS-000730]. /
lm	C7	Levy et al., "Deposition of Tungsten Nitride", Novellus Systems, Inc., filed October 20, 2003, Application No. 10/690,492, pages 1-42. [Atty Dkt. NOVLP063/NVLS-000615] /
Examiner <i>lm</i>		Date Considered <i>12-22-5</i>

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	000498X1	
	Applicant:	
	Lee et al.	
	Filing Date	Group
	August 26, 2003	1762

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
lm	C8	Fair et al., "Selective Refractory Metal and Nitride Capping", Novellus Systems, Inc., filed November 8, 2004, Appln No. 10/984,126, pages 1-22. [NOVLP058D1/NVLS-000732D1]
Examiner		Date Considered
		12-22-5

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#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
lm	A1	2002/0177316	11.2002	Miller et al.			
	A2	6,962,873	11.2005	Park, Heung L.			

#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
lm	C1	U.S. Office Action mailed November 8, 2004, from U.S. Application No. 10/984,126 [Atty Dkt. NOVLP058D1/NVLS-000732D1]. ✓
lm	C2	Chan et al., "Methods for Growing Low-Resistivity Tungsten Film", Novellus Systems, Inc., filed November 1, 2005, Application No. 11/265,531, pages 1-35. [NOVLP137/NVLS-0003093] ✓
Examiner		Date Considered
lm		12-22-5

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